

General Description

The 80N06 is N-ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

Features

- Simple Drive Requirement
- Fast Switching
- Low On-Resistance

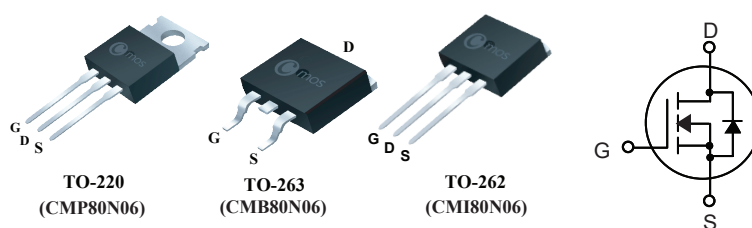
Product Summary

BVDSS	RDSON	ID
60V	8.3mΩ	80A

Applications

- Motor Control
- DC-DC converters
- General Purpose Power Amplifier

TO-220/263/262 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current ¹	80	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current ¹	50	A
I_{DM}	Pulsed Drain Current ²	320	A
EAS	Single Pulse Avalanche Energy ³	420	mJ
I_{AS}	Avalanche Current	80	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	260	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-case	0.57	$^\circ\text{C/W}$

N-Channel Enhancement Mode Field Effect Transistor

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=40A$	---	7.4	8.3	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V$, $V_{GS}=0V$	---	---	1	μA
		$V_{DS}=60V$, $V_{GS}=0V$, $T_J=125^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=40A$	---	17	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1.5	---	Ω
Q_g	Total Gate Charge	$I_D=80A$	---	76	---	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=30V$	---	24	---	
Q_{gd}	Gate-Drain Charge	$V_{GS}=0$ to $10V$	---	35	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=30V$	---	45	---	ns
T_r	Rise Time	$I_D=80A$	---	160	---	
$T_{d(off)}$	Turn-Off Delay Time	$R_G=3.3\Omega$	---	95	---	
T_f	Fall Time	$V_{GS}=10V$	---	68	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3800	---	pF
C_{oss}	Output Capacitance		---	360	---	
C_{rss}	Reverse Transfer Capacitance		---	300	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ¹	$V_G=V_D=0V$, Force Current	---	---	80	A
I_{SM}	Pulsed Source Current ²		---	---	320	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=50A$, $T_J=25^\circ\text{C}$	---	---	1.5	V

Note :

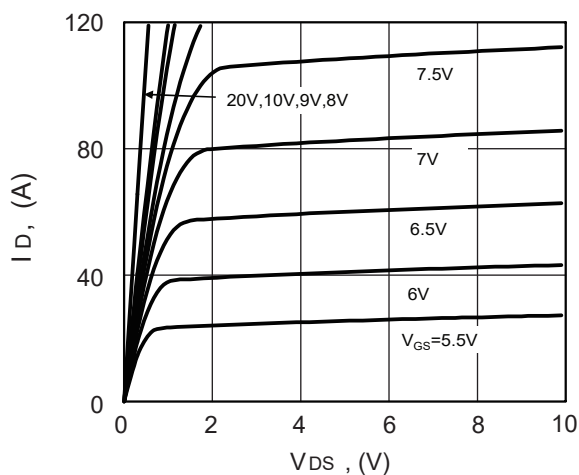
1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$ 3.The EAS data shows Max. rating . The test condition is $V_{DD}=30V$, $V_{GS}=10V$, $L=0.5\text{mH}$, $I_{AS}=41A$

This product has been designed and qualified for the consumer market.

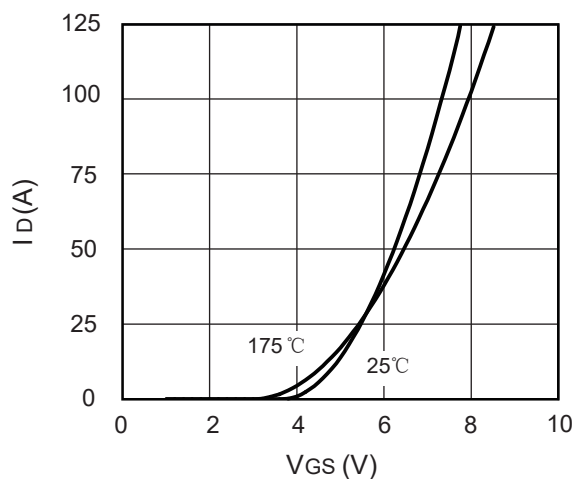
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Cmos reserves the right to improve product design ,functions and reliability without notice.

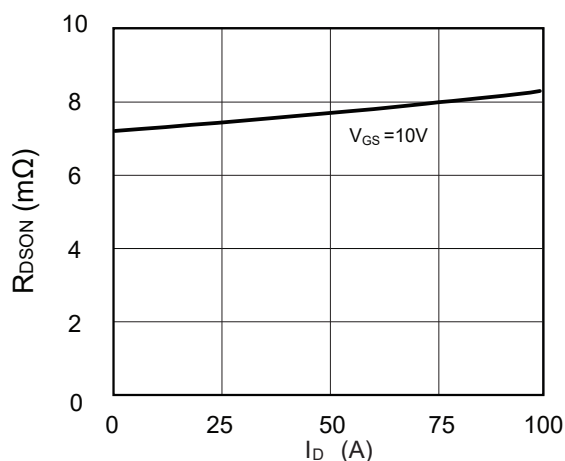
Typical Characteristics



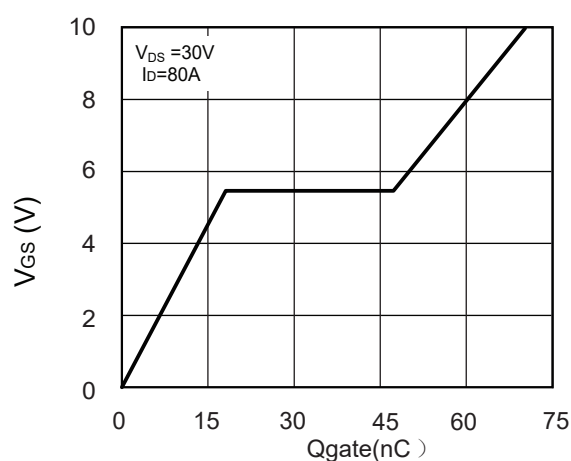
Output Characteristics



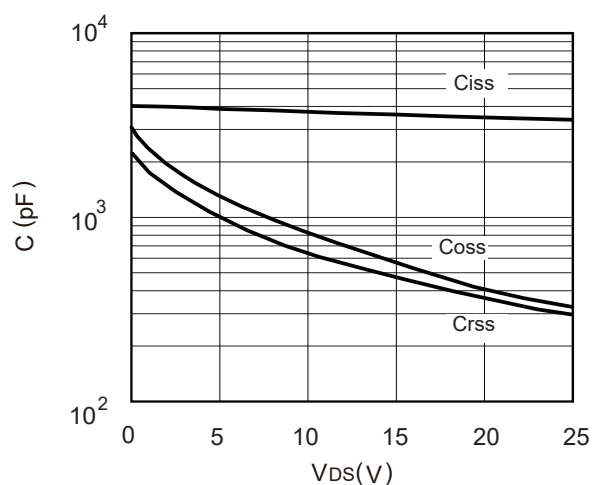
Transfer characteristics



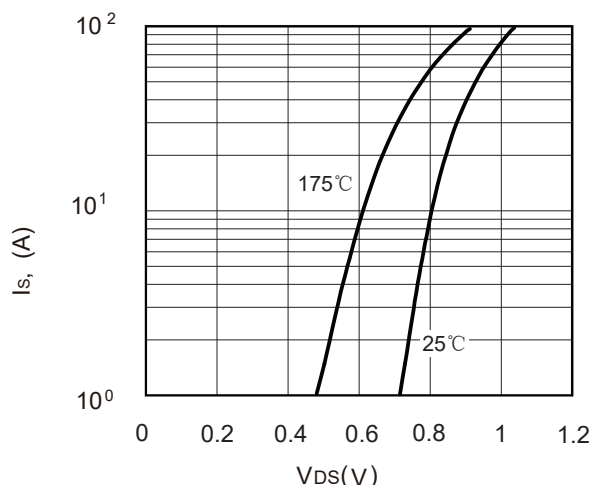
drain-source on-resistance



Gate charge vs gate-source voltage



Capacitance Characteristics



Body-Diode Characteristics